

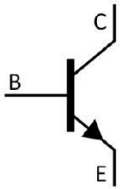
TO-220F

NPN

Silicon NPN transistor in a TO-220F Plastic Package.

High DC current gain, low $V_{CE(sat)}$, large collector power dissipation, wide SOA.

Low frequency power amplifier.



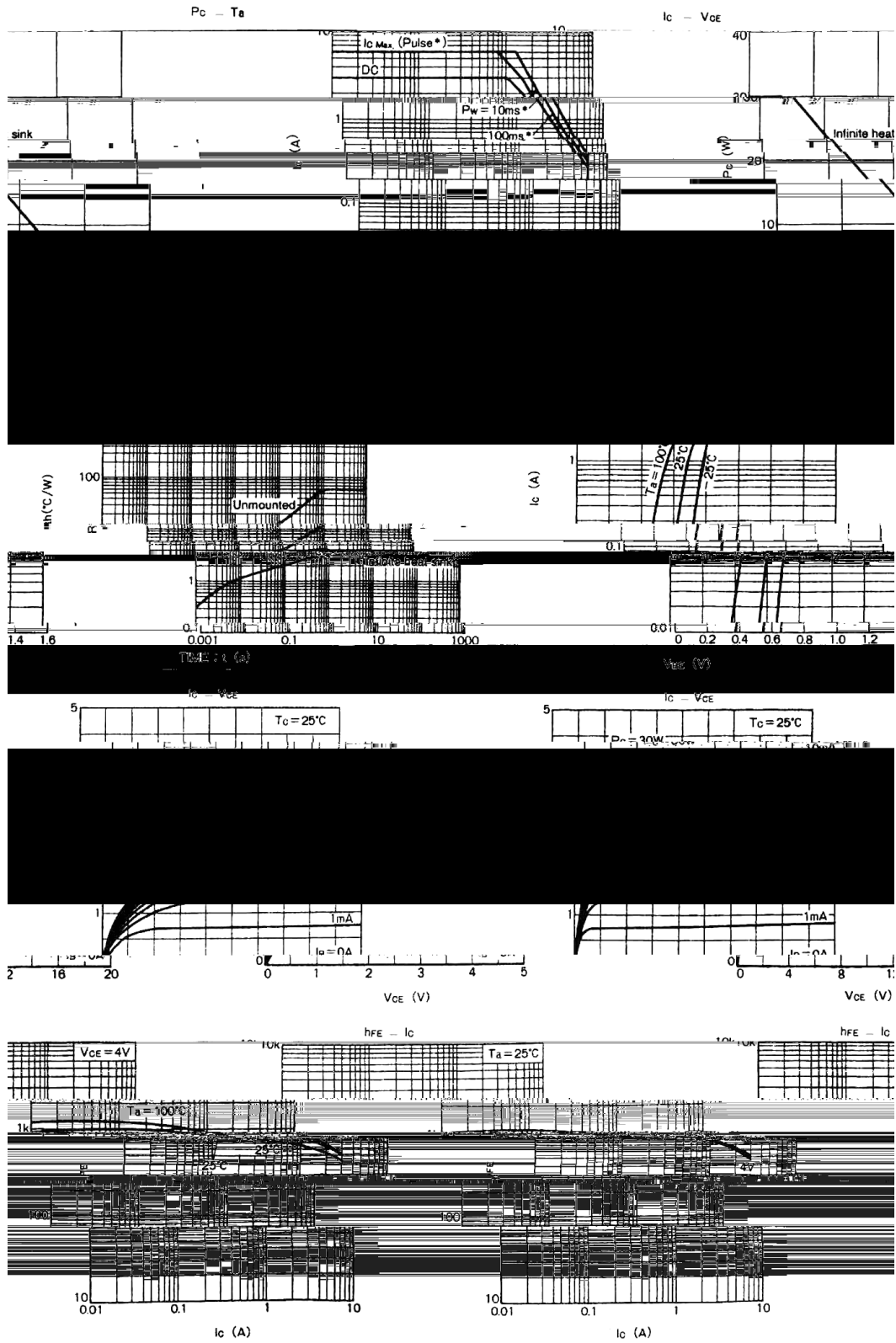
PIN1 Base

PIN 2 Collector

PIN 3 Emitter

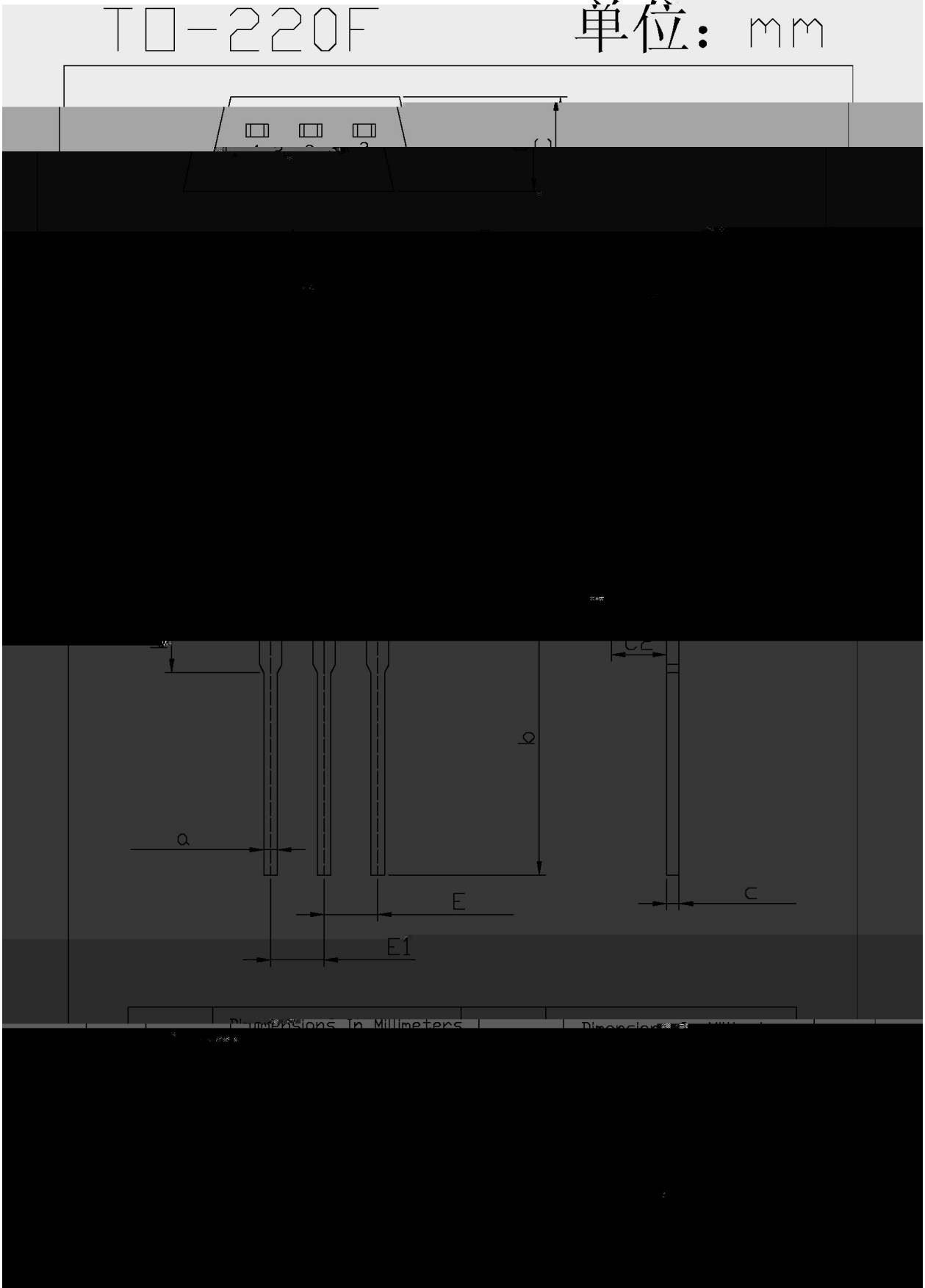
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Current – Continuous(Pulse)	I_{CP}	6.0	A
Collector Power Dissipation	P_C	2.0	W
	$P_C(T_c=25^\circ\text{C})$	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

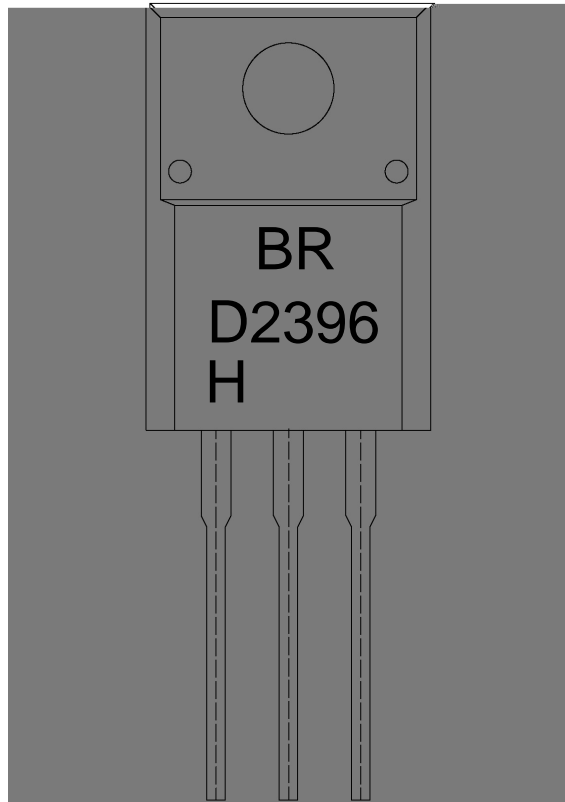
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\mu\text{A}$	80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0\text{mA}$	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=50\mu\text{A}$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=80\text{V}$ $I_E=0$			100	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=6.0\text{V}$ I_C				



TO-220F

单位: mm





BR

D2396

H: h_{FE}

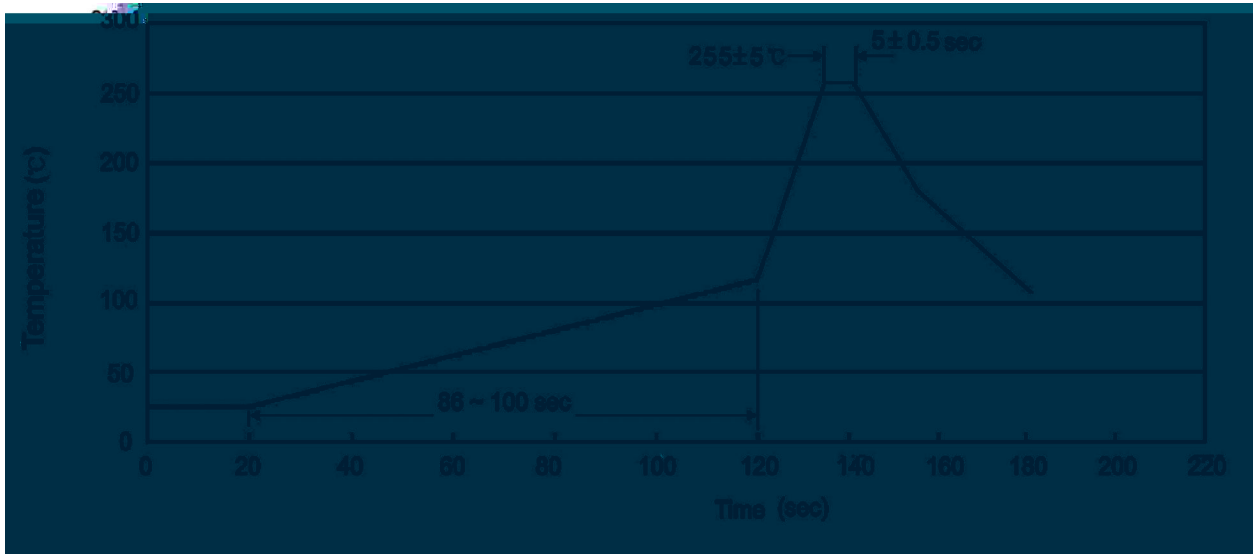
Note:

BR: Company Code.

D2396: Product Type.

H: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.


Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units	Dimension	(unit mm ³)
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